



FEATURE

- TrenchFET Power MOSFET

APPLICATION

- DC/DC Converters
- Load Switching for Portable Applications

MARKING

- MARKING: S12

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20 V	31.8mΩ@4.5V	5A
	35.6mΩ@2.5V	
	41.4mΩ@1.8V	



SOT-23

Maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±8.0	
Continuous Drain Current t=5s	I_D	5	A
Pulsed Drain Current	I_{DM}	20	
Continuous Source-Drain Diode Current	I_S	1.04	
Maximum Power Dissipation t=5s	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-50 ~+150	°C



Ta=25 °C unless otherwise specified

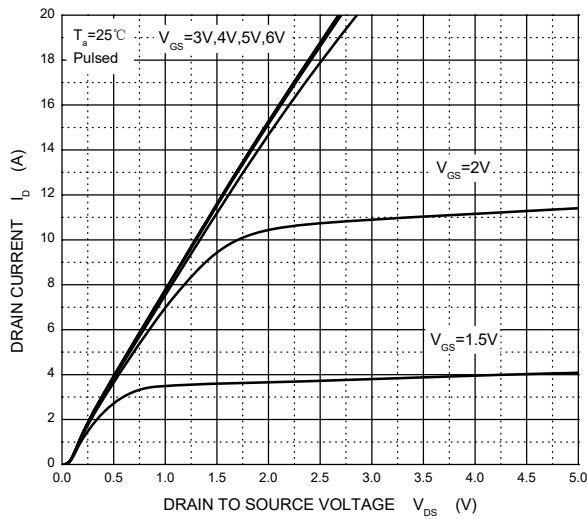
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V _(BR) DSS	V _{GS} = 0V, I _D = 250μA	20			V
Gate-source leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±8V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1.0	μA
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.45	0.7	1.0	V
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 4.5V, I _D = 5.0A		0.018	0.0318	Ω
		V _{GS} = 2.5V, I _D = 4.7A		0.023	0.0356	
		V _{GS} = 1.8V, I _D = 4.3A		0.030	0.0414	
Forward transconductance ^a	g _{fS}	V _{DS} = 10V, I _D = 5.0A		6		S
Dynamic^b						
Input capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz		865		pF
Output capacitance	C _{oss}			105		
Reverse transfer capacitance	C _{rss}			55		
Gate resistance	R _g	f = 1MHz	0.5		4.8	Ω
Turn-on delay Time	t _{d(on)}	V _{GEN} = 5V, V _{DD} = 10V, I _D = 4A, R _G = 1Ω, R _L = 2.2Ω			10	ns
Rise time	t _r				20	
Turn-off Delay time	t _{d(off)}				32	
Fall time	t _f				12	
Drain-source body diode characteristics						
Forward diode voltage	V _{SD}	V _{GS} = 0V, I _S = 4A		0.75	1.2	V

Notes :

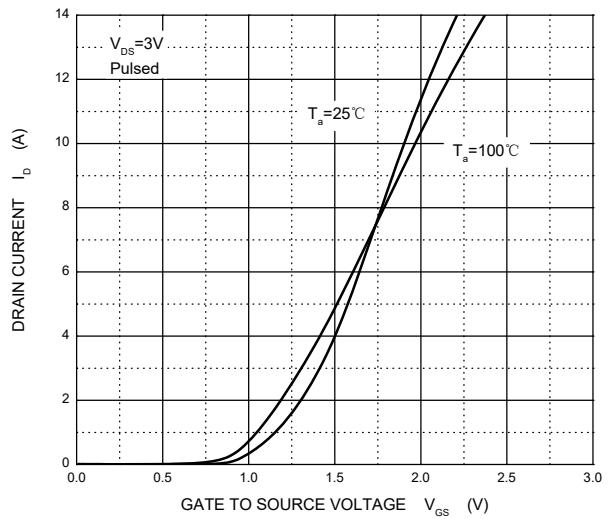
a. Pulse Test : pulse width ≤ 300μs, duty cycle ≤ 2%.

b. These parameters have no way to verify.

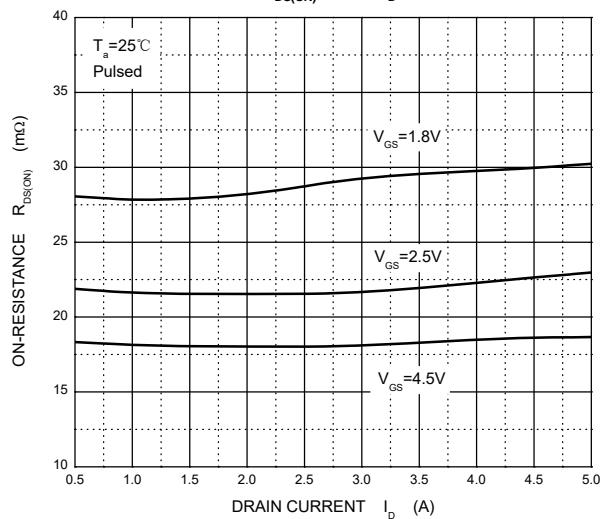
Output Characteristics



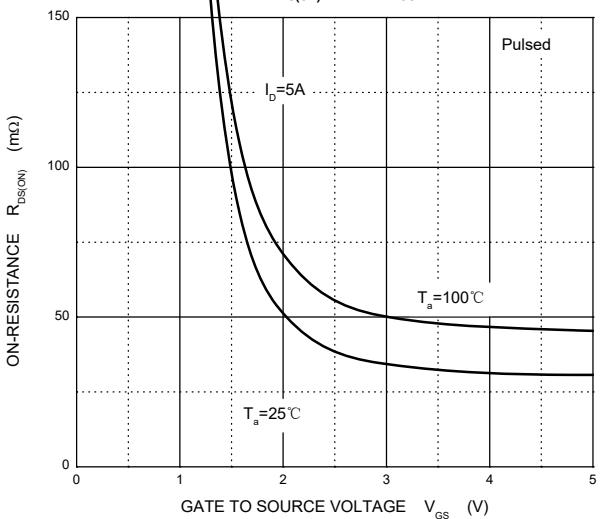
Transfer Characteristics



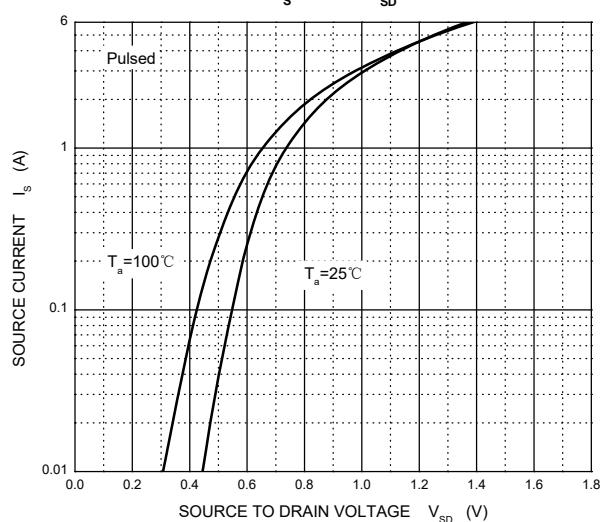
$R_{DS(ON)}$ — I_D



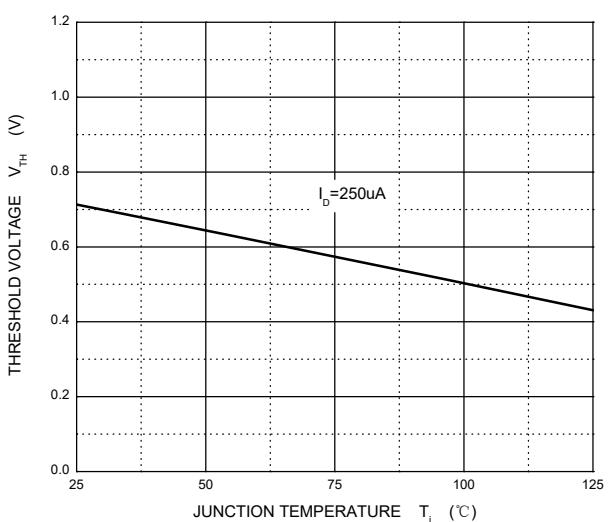
$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}

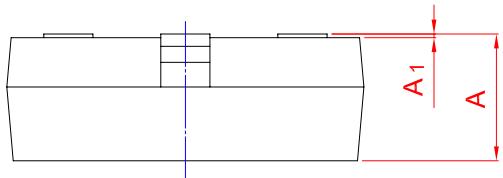
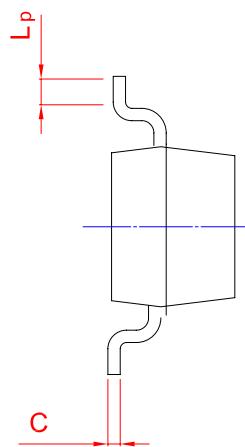
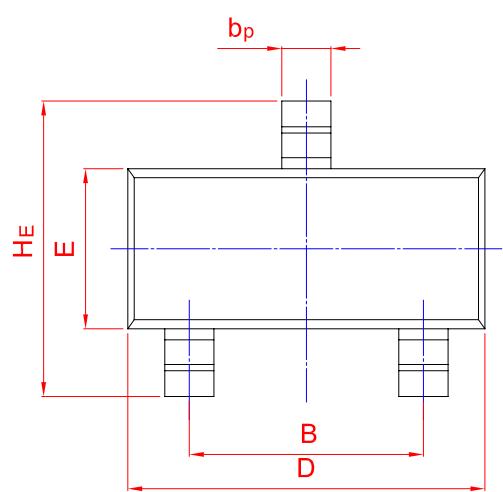


Threshold Voltage



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20